

2.9 nV/sqrt(Hz) Low Noise, RRIO Amplifier

Check for Samples: LMP7732

FEATURES

- (Typical Values, T_A = 25°C, V_S = 5V)
- Input Voltage Noise
 - f = 3 Hz 3.3 nV/ $\sqrt{\text{Hz}}$
 - f = 1 kHz 2.9 nV/ $\sqrt{\text{Hz}}$
- CMRR 130 dB
- Open Loop Gain 130 dB
- GBW 22 MHz
- Slew Rate 2.4 V/μs
- THD 0.001% @ f = 10 kHz, AV = 1, RL = 2 k Ω
- Supply Current 4.4 mA
- Supply Voltage Range 1.8V to 5.5V
- Operating Temperature Range -40°C to 125°C
- Input Bias Current ±1.5 nA
- RRIO

APPLICATIONS

- Gas Analysis Instruments
- Photometric Instrumentation
- Medical Instrumentation

DESCRIPTION

The LMP7732 is a dual low noise, rail-to-rail input and output, low voltage amplifier. The LMP7732 is part of the LMP™ amplifier family and is ideal for precision and low noise applications with low voltage requirements.

This operational amplifier offers low voltage noise of 2.9 nV/√Hz with a 1/f corner of only 3 Hz. The LMP7732 has bipolar junction input stages with a bias current of only 1.5 nA. This low input bias current, complemented by the very low level of voltage noise, makes the LMP7732 an excellent choice for photometry applications.

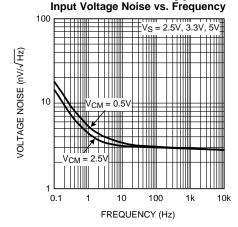
The LMP7732 provides a wide GBW of 22 MHz while consuming only 4 mA of current. This high gain bandwidth along with the high open loop gain of 130 dB enables accurate signal conditioning in applications with high closed loop gain requirements.

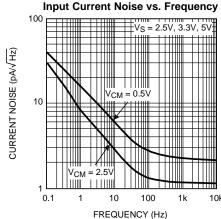
The LMP7732 has a supply voltage range of 1.8V to 5.5V, making it an ideal choice for battery operated portable applications.

The LMP7732 is offered in the 8-Pin SOIC and VSSOP packages.

The LMP7731 is the single version of this product and is offered in the 5-Pin SOT-23 and 8-Pin SOIC packages.

Typical Performance Characteristics





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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings (1)(2)

	9-						
	Lluman Rady Madal		For inputs pins only	2000V			
ESD Tolerance ⁽³⁾	Human Body Model		For all other pins	2000V			
ESD Tolerance (%)	Machine Model	Machine Model					
	Charge Device Model			1000V			
V _{IN} Differential			±2V				
Supply Voltage $(V_S = V^+ - V^-)$				6.0V			
Storage Temperature Range				-65°C to 150°C			
Junction Temperature (4)				+150°C max			
Soldering Information			Infrared or Convection (20 sec)	235°C			
			Wave Soldering Lead Temp. (10 sec)	260°C			

- (1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics Tables.
- (2) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.
- (3) Human Body Model, applicable std. MIL-STD-883, Method 3015.7. Machine Model, applicable std. JESD22-A115-A (ESD MM std. of JEDEC) Field-Induced Charge-Device Model, applicable std. JESD22-C101-C (ESD FICDM std. of JEDEC).
- (4) The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} , and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} T_A)/(\theta_{JA})$. All numbers apply for packages soldered directly onto a PC board.

Operating Ratings⁽¹⁾

<u> </u>		
Temperature Range		-40°C to 125°C
Supply Voltage $(V_S = V^+ - V^-)$	1.8V to 5.5V	
Package Thermal Pacietones (0.)	8-Pin SOIC	190 °C/W
Package Thermal Resistance (θ _{JA})	8-Pin VSSOP	235°C/W

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics Tables.



2.5V Electrical Characteristics⁽¹⁾

Unless otherwise specified, all limits are ensured for $T_A = 25^{\circ}C$, $V^+ = 2.5V$, $V^- = 0V$, $V_{CM} = V^+/2$, $R_L > 10 \text{ k}\Omega$ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units		
\/	Input Offset Voltage (4)	V _{CM} = 2.0V		±9	±500 ±600	\/		
V _{OS}	Input Offset Voltage (4)	V _{CM} = 0.5V		±9	±500 ±600	μV		
TCV	Input Offeet Veltage Temperature Drift	V _{CM} = 2.0V		±0.5	±5.5	μV/°C		
TCV _{OS}	Input Offset Voltage Temperature Drift	V _{CM} = 0.5V		±0.2	±5.5	μν/ С		
I _B	Input Bias Current	V _{CM} = 2.0V		±1	±30 ± 45	nA		
'B	Input Bido Garront	$V_{CM} = 0.5V$		±12	±50 ±75	10.0		
laa	Input Offset Current	V _{CM} = 2.0V		±1	±50 ±75	nA		
los	input Onset Current	tt Offset Current $V_{CM} = 0.5V \pm 1$						
TCI _{OS}	Input Offset Current Drift	$V_{CM} = 0.5V$ and $V_{CM} = 2.0V$		0.0474		nA/°C		
CMDD	Common Mode Dejection Detic	$0.15V \le V_{CM} \le 0.7V$ $0.23V \le V_{CM} \le 0.7V$	101 89	120		٩D		
CMRR	Common Mode Rejection Ratio	$1.5V \le V_{CM} \le 2.35V$ $1.5V \le V_{CM} \le 2.27V$	105 99	129		dB		
PSRR	Power Supply Rejection Ratio	2.5V ≤ V ⁺ ≤ 5V	105 101	113		dB		
Ortic	, , ,	1.8V ≤ V ⁺ ≤ 5.5V		111				
CMVR	Common Mode Voltage Range	Large Signal CMRR ≥ 80 dB	0		2.5	V		
۸	0 1 1/1 0:	$R_L = 10 \text{ k}\Omega \text{ to V}^+/2$ $V_{OUT} = 0.5 \text{V to } 2.0 \text{V}$	112 104	130		dB		
A _{VOL}	Open Loop Voltage Gain	$R_L = 2 k\Omega$ to $V^+/2$ $V_{OUT} = 0.5V$ to 2.0V	109 90	119		ив		
	Output Voltage Swing High	$R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		4	50 75			
V _{OUT}	Output Voltage Swillig Flight	$R_L = 2 k\Omega$ to $V^+/2$		13	50 75	mV from		
V 001	Output Voltage Swing Low	$R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		6	50 75	either rail		
	Output Voltage Owing Low	$R_L = 2 k\Omega$ to $V^+/2$		9	50 75			
ı	Output Current	Sourcing, $V_{OUT} = V^+/2$ V_{IN} (diff) = 100 mV	22 12	31				
lout	Output Current	Sinking, $V_{OUT} = V^{+}/2$ V_{IN} (diff) = -100 mV	15 10	44		mA		
1	Supply Current	V _{CM} = 2.0V		4.0	5.4 6.8	m ^		
I _S	Зирріу Сипепі	V _{CM} = 0.5V		4.6	6.2 7.8	mA		
SR	Slew Rate	$A_V = +1$, $C_L = 10$ pF, $R_L = 10$ k Ω to $V^+/2$ $V_{OUT} = 2$ V_{PP}		2.4		V/µs		
	+	-+						

⁽¹⁾ Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that T_J = T_A. No ensured specification of parametric performance is indicated in the electrical tables under conditions of internal self-heating where T_J > T_A. Absolute maximum Ratings indicate junction temperature limits beyond which the device maybe permanently degraded, either mechanically or electrically.

⁽²⁾ All limits are specified by testing, statistical analysis or design.

⁽³⁾ Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not ensured on shipped production material.

⁴⁾ Ambient production test is performed at 25°C with a variance of ±3°C.



2.5V Electrical Characteristics⁽¹⁾ (continued)

Unless otherwise specified, all limits are ensured for $T_A = 25^{\circ}C$, $V^+ = 2.5V$, $V^- = 0V$, $V_{CM} = V^+/2$, $R_L > 10 \text{ k}\Omega$ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units	
GBW	Gain Bandwidth	$C_L = 20 \text{ pF}, R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		21		MHz	
G _M	Gain Margin	$C_L = 20 \text{ pF}, R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		14		dB	
ФМ	Phase Margin	$C_L = 20 \text{ pF}, R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		60		deg	
Б	Innut Decistores	Differential Mode		38		kΩ	
R _{IN}	Input Resistance	Common Mode		151	ΜΩ		
THD+N	Total Harmonic Distortion + Noise	$A_V = 1$, $f_O = 1$ kHz, Amplitude = 1V		0.002		%	
	land Defended Voltage Naise Descite	f = 1 kHz, V _{CM} = 2.0V		3.0		nV/√ Hz	
e_n	Input Referred Voltage Noise Density	$f = 1 \text{ kHz}, V_{CM} = 0.5V$		3.0		IIV/VIIZ	
	Input Voltage Noise	0.1 Hz to 10 Hz		75		nV_PP	
	Innut Referred Current Naise Renaits	f = 1 kHz, V _{CM} = 2.0V		1.1		- A /-/II=	
ın	Input Referred Current Noise Density	f = 1 kHz, V _{CM} = 0.5V		2.3		pA/√ Hz	

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3.3V Electrical Characteristics(1)

Unless otherwise specified, all limits are ensured for $T_A = 25^{\circ}C$, $V^+ = 3.3V$, $V^- = 0V$, $V_{CM} = V^+/2$, $R_L > 10~k\Omega$ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units	
\/	Innut Officet Vallage (4)	V _{CM} = 2.5V		±6	±500 ± 600	/	
V _{OS}	Input Offset Voltage (4)	V _{CM} = 0.5V		±6	±500 ± 600	μV	
TOV	Input Offset Voltage Temperature	V _{CM} = 2.5V		±0.5	±5.5	\//90	
TCV _{OS}	Drift	V _{CM} = 0.5V		±0.2	±5.5	μV/°C	
	Input Pigg Current	V _{CM} = 2.5V		±1.5	±30 ±45	^	
I _B	Input Bias Current	V _{CM} = 0.5V		±13	±50 ±77	nA	
	Input Offset Current	V _{CM} = 2.5V		±1	±50 ±70	- ^	
los	Input Offset Current	V _{CM} = 0.5V		±11	±60 ±80	nA	
TCI _{OS}	Input Offset Current Drift	$V_{CM} = 0.5V$ and $V_{CM} = 2.5V$		0.048		nA/°C	
CMDD	Common Mada Baisating Batis	$0.15V \le V_{CM} \le 0.7V$ $0.23V \le V_{CM} \le 0.7V$	101 89	120		-10	
CMRR	Common Mode Rejection Ratio	$1.5V \le V_{CM} \le 3.15V$ $1.5V \le V_{CM} \le 3.07V$	105 99	130		dB	
PSRR	Power Supply Rejection Ratio	2.5V ≤ V ⁺ ≤ 5.0V	105 101	113		dB	
	,	1.8V ≤ V ⁺ ≤ 5.5V		111			
CMVR	Common Mode Voltage Range	Large Signal CMRR ≥ 80 dB	0		3.3	V	
^	On and Lean Valle on Cain	$R_L = 10 \text{ k}\Omega \text{ to V}^+/2$ $V_{OUT} = 0.5 \text{V to } 2.8 \text{V}$	112 104	130		-10	
A _{VOL}	Open Loop Voltage Gain	$R_L = 2 k\Omega \text{ to } V^+/2$ $V_{OUT} = 0.5V \text{ to } 2.8V$	110 92	119		dB	
	Output Valtage Code at High	$R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		5	50 75		
M	Output Voltage Swing High	$R_L = 2 k\Omega$ to V ⁺ /2		14	50 75	mV from	
V _{OUT}	Output Voltage Swing Low	$R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		9	50 75	either rail	
	Output Voltage Swing Low	$R_L = 2 k\Omega \text{ to } V^+/2$		13	50 75		
	Output Comment	Sourcing, $V_{OUT} = V^{+}/2$ V_{IN} (diff) = 100 mV	28 22	45		Λ	
l _{OUT}	Output Current	Sinking, $V_{OUT} = V^+/2$ V_{IN} (diff) = -100 mV	25 20	48		mA	
	Supply Correct	V _{CM} = 2.5V		4.2	5.6 7.0	mA	
I _S	Supply Current	V _{CM} = 0.5V		4.8	6.4 8.0		
SR	Slew Rate	$A_V = +1$, $C_L = 10$ pF, $R_L = 10$ k Ω to $V^+/2$ $V_{OUT} = 2$ V_{PP}		2.4		V/µs	

⁽¹⁾ Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that $T_J = T_A$. No ensured specification of parametric performance is indicated in the electrical tables under conditions of internal self-heating where T_J > T_A. Absolute maximum Ratings indicate junction temperature limits beyond which the device maybe permanently degraded, either mechanically or electrically.

All limits are specified by testing, statistical analysis or design.

Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not ensured on shipped production material.

Ambient production test is performed at 25°C with a variance of ±3°C.



3.3V Electrical Characteristics⁽¹⁾ (continued)

Unless otherwise specified, all limits are ensured for $T_A = 25^{\circ}C$, $V^+ = 3.3V$, $V^- = 0V$, $V_{CM} = V^+/2$, $R_L > 10 \text{ k}\Omega$ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units
GBW	Gain Bandwidth	$C_L = 20 \text{ pF}, R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		22		MHz
G _M	Gain Margin	$C_L = 20 \text{ pF}, R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		14		dB
ФМ	Phase Margin	$C_L = 20 \text{ pF}, R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		62		deg
THD+N	Total Harmonic Distortion + Noise	$A_V = 1$, $f_O = 1$ kHz, Amplitude = 1V		0.002		%
_	land Decistors	Differential Mode		38		kΩ
R _{IN}	Input Resistance	Common Mode		151		ΜΩ
	Input Referred Voltage Noise	f = 1 kHz, V _{CM} = 2.5V		2.9		nV/√Hz
e _n	Density	f = 1 kHz, V _{CM} = 0.5V		2.9		
	Input Voltage Noise	0.1 Hz to 10 Hz		75		nV_{PP}
	Input Referred Current Noise	f = 1 kHz, V _{CM} = 2.5V		1.1		pA/√Hz
In	Density	f = 1 kHz, V _{CM} = 0.5V		2.1		

5V Electrical Characteristics (1)

Unless otherwise specified, all limits are ensured for $T_A = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_{CM} = V^+/2$, $R_L > 10 \text{ k}\Omega$ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units
V	Input Offset Voltage (4)	V _{CM} = 4.5V		±6	±500 ±600	\/
V _{OS}	Input Offset Voltage V	V _{CM} = 0.5V		±6	±500 ± 600	μV
TCV	Input Offeet Veltage Temperature Drift	V _{CM} = 4.5V		±0.5	±5.5	\//00
TCV _{OS}	Input Offset Voltage Temperature Drift	V _{CM} = 0.5V		±0.2	±5.5	μV/°C
	Input Dica Current	V _{CM} = 4.5V		±1.5	±30 ±50	~^
l _B	Input Bias Current	V _{CM} = 0.5V		±14	±50 ±85	nA
	land Offset Comment	V _{CM} = 4.5V		±1	±50 ±70	Λ
los	Input Offset Current	V _{CM} = 0.5V		±11	±65 ± 80	nA
TCI _{OS}	Input Offset Current Drift	V _{CM} = 0.5V and V _{CM} = 4.5V		0.0482		nA/°C
CMRR	Common Mada Deigation Detic	$0.15V \le V_{CM} \le 0.7V$ $0.23V \le V_{CM} \le 0.7V$	101 89	120		-10
CIVIRR	Common Mode Rejection Ratio	$1.5V \le V_{CM} \le 4.85V$ $1.5V \le V_{CM} \le 4.77V$	105 99	130		dB
PSRR	Power Supply Rejection Ratio	2.5V ≤ V ⁺ ≤ 5V	105 101	113		dB
	11,3	1.8V ≤ V ⁺ ≤ 5.5V		111		
CMVR	Common Mode Voltage Range	Large Signal CMRR ≥ 80 dB	0		5	V
۸	Onen Leen Veltage Cein	$R_L = 10 \text{ k}\Omega \text{ to V}^+/2$ $V_{OUT} = 0.5 \text{V to } 4.5 \text{V}$	112 104	130		dB
A _{VOL}	Open Loop Voltage Gain	$R_L = 2 k\Omega \text{ to V}^+/2$ $V_{OUT} = 0.5V \text{ to } 4.5V$	110 94	119		uв

⁽¹⁾ Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that T_J = T_A. No ensured specification of parametric performance is indicated in the electrical tables under conditions of internal self-heating where T_J > T_A. Absolute maximum Ratings indicate junction temperature limits beyond which the device maybe permanently degraded, either mechanically or electrically.

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⁽³⁾ Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not ensured on shipped production material.

⁽⁴⁾ Ambient production test is performed at 25°C with a variance of ±3°C.



5V Electrical Characteristics⁽¹⁾ (continued)

Unless otherwise specified, all limits are ensured for $T_A = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_{CM} = V^+/2$, $R_L > 10 k\Omega$ to $V^+/2$. **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units
	Output Valle as Output High	$R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		8	50 75	
\	Output Voltage Swing High	$R_L = 2 k\Omega$ to V ⁺ /2		24	50 75	mV from
V _{OUT}	Output Voltage Suing Law	$R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		9	50 75	either rail
	Output Voltage Swing Low	$R_L = 2 k\Omega$ to $V^+/2$		23	50 75	
	Output Current	Sourcing, $V_{OUT} = V^{+}/2$ V_{IN} (diff) = 100 mV	33 27	47		mA
I _{OUT}	Output Current	30 25	49		IIIA	
I.	Supply Current	V _{CM} = 4.5V		4.4	6.0 7.4	A
I _S	Supply Current	V _{CM} = 0.5V		5.0	6.8 8.4	mA mA
SR	Slew Rate	A_V = +1, C_L = 10 pF, R_L = 10 k Ω to $V^+/2$ V_{OUT} = 2 V_{PP}		2.4		V/µs
GBW	Gain Bandwidth	$C_L = 20 \text{ pF}, R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		22		MHz
G _M	Gain Margin	$C_L = 20 \text{ pF}, R_L = 10 \text{ k}\Omega \text{ to V}^+/2$		12		dB
ФМ	Phase Margin	$C_L = 20 \text{ pF}, R_L = 10 \text{ k}\Omega \text{ to V}^+\!/2$		65		deg
D	January Designation of	Differential Mode		38		kΩ
R _{IN}	Input Resistance	Common Mode		151		ΜΩ
THD+ N	Total Harmonic Distortion + Noise	$A_V = 1$, $f_O = 1$ kHz, Amplitude = 1V		0.001		%
	Law to Defermed Veltere Naise Descit.	f = 1 kHz, V _{CM} = 4.5V		2.9		-> // ₂ /1.
e _n	Input Referred Voltage Noise Density	f = 1 kHz, V _{CM} = 0.5V		2.9		nV/√Hz
	Input Voltage Noise	0.1 Hz to 10 Hz		75		nV_{PP}
	Input Referred Current Noice Descitu	f = 1 kHz, V _{CM} = 4.5V		1.1		pA/√Hz
i _n	Input Referred Current Noise Density	f = 1 kHz, V _{CM} = 0.5V		2.2		PAVVHZ

Connection Diagram

8-Pin SOIC/VSSOP

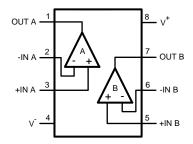


Figure 1. Top View



Typical Performance Characteristics

Unless otherwise noted: $T_A = 25$ °C, $R_L > 10 \text{ k}\Omega$, $V_{CM} = V_S/2$.

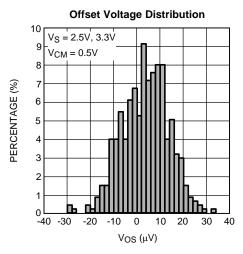


Figure 2.

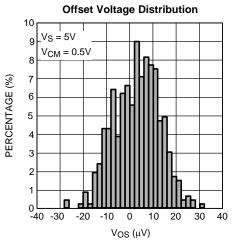


Figure 4.

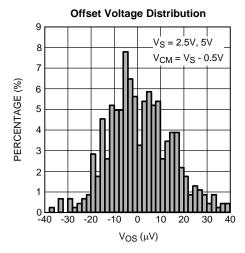


Figure 6.

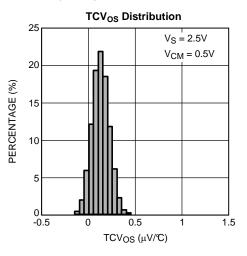


Figure 3.

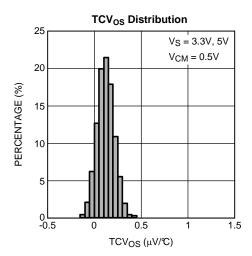


Figure 5.

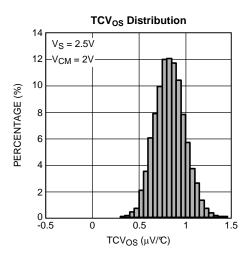


Figure 7.

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Unless otherwise noted: $T_A = 25$ °C, $R_L > 10 \text{ k}\Omega$, $V_{CM} = V_S/2$.

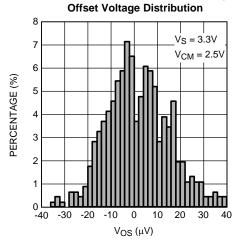


Figure 8.

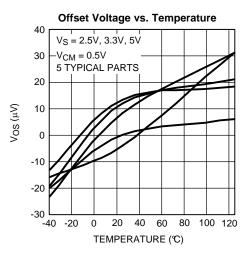


Figure 10.

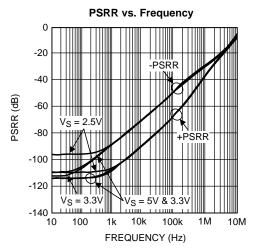


Figure 12.

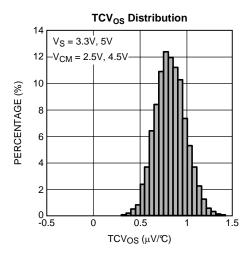


Figure 9.

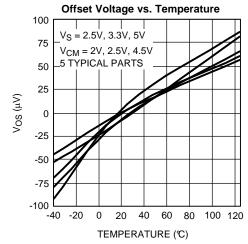


Figure 11.

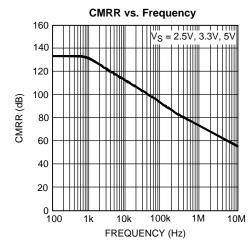


Figure 13.



Unless otherwise noted: T_A = 25°C, R_L > 10 k Ω , V_{CM} = $V_S/2$.

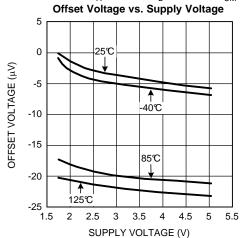
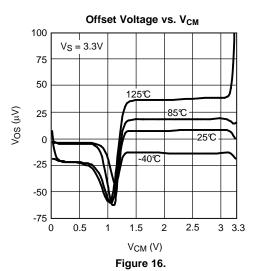
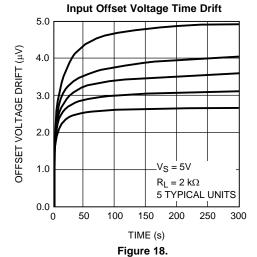


Figure 14.





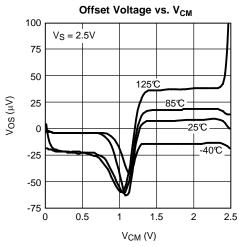


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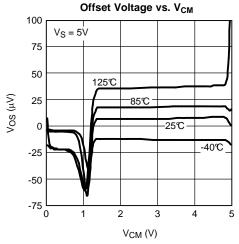
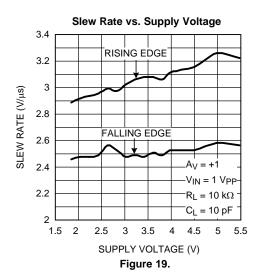


Figure 17.



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Unless otherwise noted: T_A = 25°C, R_L > 10 k Ω , V_{CM} = $V_S/2$.

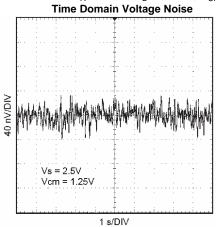


Figure 20.

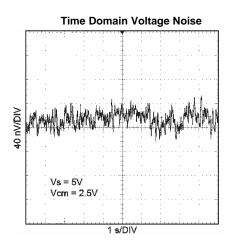
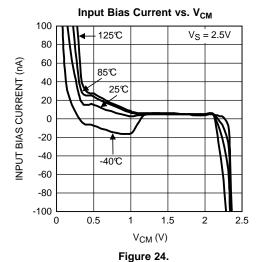


Figure 22.



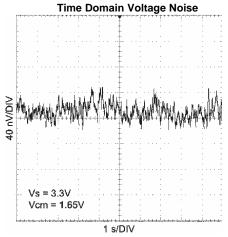
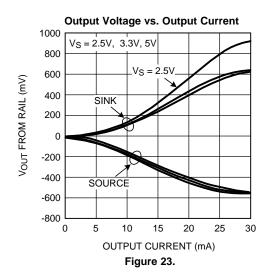


Figure 21.



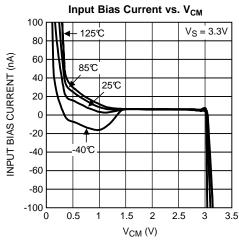


Figure 25.

i iguie 25.



Unless otherwise noted: $T_A = 25$ °C, $R_L > 10 \text{ k}\Omega$, $V_{CM} = V_S/2$.

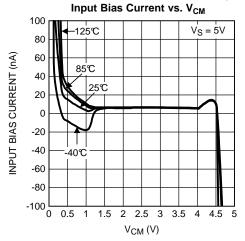


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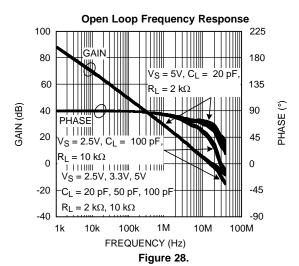


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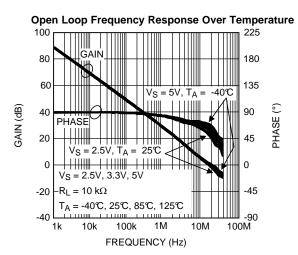
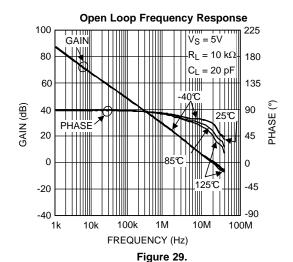
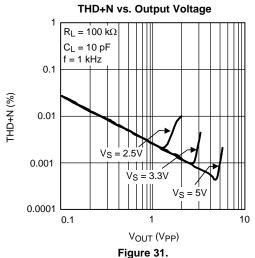


Figure 27.





rigure 31.

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Unless otherwise noted: T_A = 25°C, R_L > 10 k Ω , V_{CM} = $V_S/2$.

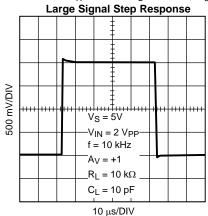


Figure 32.

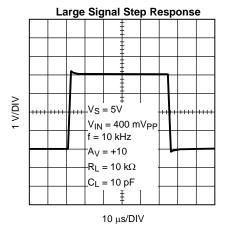
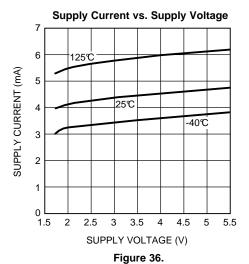


Figure 34.



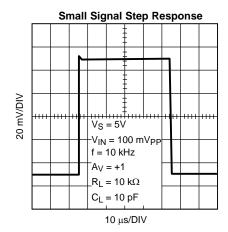


Figure 33.

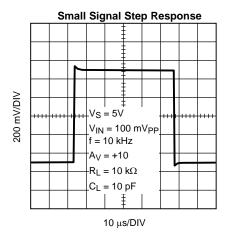


Figure 35.

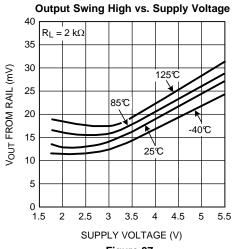
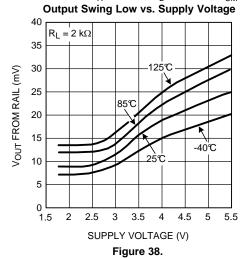
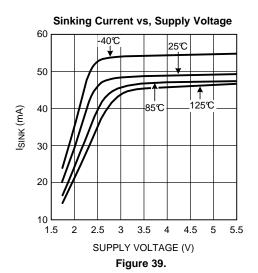


Figure 37.



Unless otherwise noted: T_A = 25°C, R_L > 10 k Ω , V_{CM} = $V_S/2$.





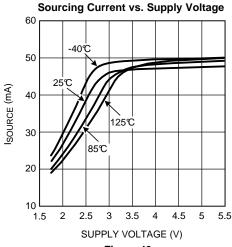


Figure 40.

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APPLICATION NOTES

LMP7732

The LMP7732 is a dual low noise, rail-to-rail input and output, low voltage amplifier.

The low input voltage noise of only 2.9 nV/ $\sqrt{\text{Hz}}$ with a 1/f corner at 3 Hz makes the LMP7732 ideal for sensor applications where DC accuracy is of importance.

The LMP7732 has high gain bandwidth of 22 MHz. This wide bandwidth enables the use of the amplifier at higher gain settings while retaining ample usable bandwidth for the application. This is particularly beneficial when system designers need to use sensors with very limited output voltage range as it allows larger gains in one stage which in turn increases signal to noise ratio.

The LMP7732 has a proprietary input bias cancellation circuitry on the input stages. This allows the LMP7732 to have only about 1.5 nA bias current with a bipolar input stage. This low input bias current, paired with the inherent lower input voltage noise of bipolar input stages makes the LMP7732 an excellent choice for precision applications. The combination of low input bias current, low input offset voltage, and low input voltage noise enables the user to achieve unprecedented accuracy and higher signal integrity.

Texas Instruments is heavily committed to precision amplifiers and the market segment they serve. Technical support and extensive characterization data is available for sensitive applications or applications with a constrained error budget.

The LMP7732 comes in the 8-Pin SOIC and VSSOP packages. These small packages are ideal solutions for area constrained PC boards and portable electronics.

INPUT BIAS CURRENT CANCELLATION

The LMP7732 has proprietary input bias current cancellation circuitry on its input stage.

The LMP7732 has rail-to-rail input. This is achieved by having a p-input and n-input stage in parallel. Figure 41 only shows one of the input stages as the circuitry is symmetrical for both stages.

Figure 41 shows that as the common mode voltage gets closer to one of the extreme ends, current I_1 significantly increases. This increased current shows as an increase in voltage drop across resistor R_1 equal to I_1*R_1 on IN+ of the amplifier. This voltage contributes to the offset voltage of the amplifier. When common mode voltage is in the mid-range, the transistors are operating in the linear region and I_1 is significantly small. The voltage drop due to I_1 across R_1 can be ignored as it is orders of magnitude smaller than the amplifier's input offset voltage. As the common mode voltage gets closer to one of the rails, the offset voltage generated due to I_1 increases and becomes comparable to the amplifiers offset voltage.

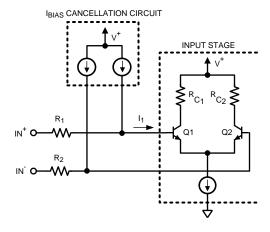


Figure 41. Input Bias Current Cancellation



INPUT VOLTAGE NOISE MEASUREMENT

The LMP7732 has very low input voltage noise. The peak-to-peak input voltage noise of the LMP7732 can be measured using the test circuit shown in Figure 42.

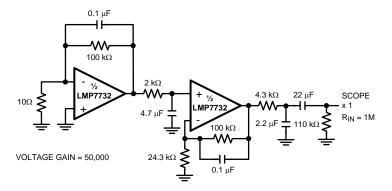


Figure 42. 0.1 Hz to 10 Hz Noise Test Circuit

The frequency response of this noise test circuit at the 0.1 Hz corner is defined by only one zero. The test time for the 0.1 Hz to 10 Hz noise measurement using this configuration should not exceed 10 seconds, as this time limit acts as an additional zero to reduce or eliminate the contributions of noise from frequencies below 0.1 Hz.

Figure 43 shows typical peak-to-peak noise for the LMP7732 measured with the circuit in Figure 42.

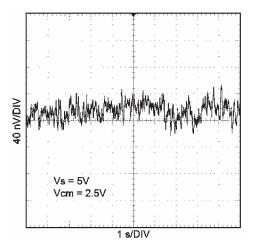


Figure 43. 0.1 Hz to 10 Hz Input Voltage Noise

Measuring the very low peak-to-peak noise performance of the LMP7732, requires special testing attention. In order to achieve accurate results, the device should be warmed up for at least five minutes. This is so that the input offset voltage of the op amp settles to a value. During this warm up period, the offset can typically change by a few μV because the chip temperature increases by about 30°C. If the 10 seconds of the measurement is selected to include this warm up time, some of this temperature change might show up as the measured noise. Figure 44 shows the start-up drift of five typical LMP7732 units.



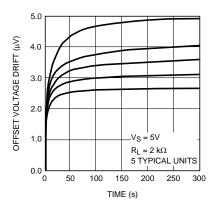


Figure 44. Start-Up Input Offset Voltage Drift

During the peak-to-peak noise measurement, the LMP7732 must be shielded. This prevents offset variations due to airflow. Offset can vary by a few nV due to this airflow and that can invalidate measurements of input voltage noise with a magnitude which is in the same range. For similar reasons, sudden motions must also be restricted in the vicinity of the test area. The feed-through which results from this motion could increase the observed noise value which in turn would invalidate the measurement.

DIODES BETWEEN THE INPUTS

The LMP7732 has a set of anti-parallel diodes between their input pins, as shown in Figure 45. These diodes are present to protect the input stage of the amplifiers. At the same time, they limit the amount of differential input voltage that is allowed on the input pins. A differential signal larger than the voltage needed to turn on the diodes might cause damage to the diodes. The differential voltage between the input pins should be limited to ±3 diode drops or the input current needs to be limited to ±20 mA.

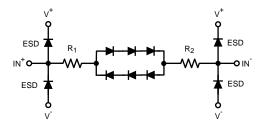


Figure 45. Anti-Parallel Diodes between Inputs

DRIVING AN ADC

Analog to Digital Converters, ADCs, usually have a sampling capacitor on their input. When the ADC's input is directly connected to the output of the amplifier a charging current flows from the amplifier to the ADC. This charging current causes a momentary glitch that can take some time to settle. There are different ways to minimize this effect. One way is to slow down the sampling rate. This method gives the amplifier sufficient time to stabilize its output. Another way to minimize the glitch, caused by the switch capacitor, is to have an external capacitor connected to the input of the ADC. This capacitor is chosen so that its value is much larger than the internal switching capacitor and it will hence provide the charge needed to quickly and smoothly charge the ADC's sampling capacitor. Since this large capacitor will be loading the output of the amplifier as well, an isolation resistor is needed between the output of the amplifier and this capacitor. The isolation resistor, $R_{\rm ISO}$, separates the additional load capacitance from the output of the amplifier and will also form a low-pass filter and can be designed to provide noise reduction as well as anti-aliasing. The draw back of having $R_{\rm ISO}$ is that it reduces signal swing since there is some voltage drop across it.

Figure 46 (a) shows the ADC directly connected to the amplifier. To minimize the glitch in this setting, a slower sample rate needs to be used. Figure 46 (b) shows $R_{\rm ISO}$ and an external capacitor used to minimize the glitch.



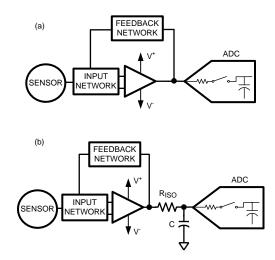


Figure 46. Driving An ADC



REVISION HISTORY

Changes from Revision D (March 2013) to Revision E						
•	Changed layout of National Data Sheet to TI format		18			

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24-Jul-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
LMP7732MA/NOPB	Active	Production	SOIC (D) 8	95 TUBE	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LMP77 32MA
LMP7732MA/NOPB.A	Active	Production	SOIC (D) 8	95 TUBE	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LMP77 32MA
LMP7732MAX/NOPB	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LMP77 32MA
LMP7732MAX/NOPB.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	LMP77 32MA
LMP7732MM/NOPB	Active	Production	VSSOP (DGK) 8	1000 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-	AZ3A
LMP7732MM/NOPB.A	Active	Production	VSSOP (DGK) 8	1000 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	AZ3A
LMP7732MM/NOPB.B	Active	Production	VSSOP (DGK) 8	1000 SMALL T&R	-	SN	Level-1-260C-UNLIM	-40 to 125	AZ3A
LMP7732MME/NOPB	Active	Production	VSSOP (DGK) 8	250 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-	AZ3A
LMP7732MME/NOPB.A	Active	Production	VSSOP (DGK) 8	250 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	AZ3A
LMP7732MME/NOPB.B	Active	Production	VSSOP (DGK) 8	250 SMALL T&R	-	SN	Level-1-260C-UNLIM	-40 to 125	AZ3A
LMP7732MMX/NOPB	Active	Production	VSSOP (DGK) 8	3500 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-	AZ3A
LMP7732MMX/NOPB.A	Active	Production	VSSOP (DGK) 8	3500 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	AZ3A
LMP7732MMX/NOPB.B	Active	Production	VSSOP (DGK) 8	3500 LARGE T&R	-	SN	Level-1-260C-UNLIM	-40 to 125	AZ3A

⁽¹⁾ Status: For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.



PACKAGE OPTION ADDENDUM

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(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

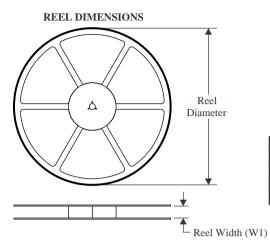
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMP7732MAX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LMP7732MM/NOPB	VSSOP	DGK	8	1000	177.8	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMP7732MME/NOPB	VSSOP	DGK	8	250	177.8	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMP7732MMX/NOPB	VSSOP	DGK	8	3500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

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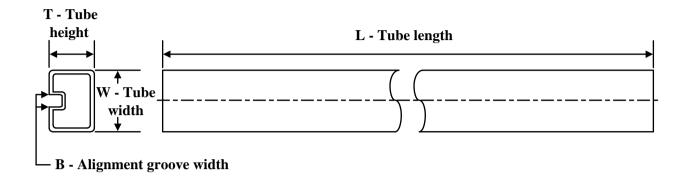
*All dimensions are nominal

Device	Package Type	Package Drawing	rawing Pins SPQ Length (mr		Length (mm)	Width (mm)	Height (mm)
LMP7732MAX/NOPB	SOIC	D	8	2500	356.0	356.0	35.0
LMP7732MM/NOPB	VSSOP	DGK	8	1000	208.0	191.0	35.0
LMP7732MME/NOPB	VSSOP	DGK	8	250	208.0	191.0	35.0
LMP7732MMX/NOPB	VSSOP	DGK	8	3500	356.0	356.0	35.0

PACKAGE MATERIALS INFORMATION

www.ti.com 1-Aug-2025

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
LMP7732MA/NOPB	D	SOIC	8	95	495	8	4064	3.05
LMP7732MA/NOPB.A	D	SOIC	8	95	495	8	4064	3.05



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



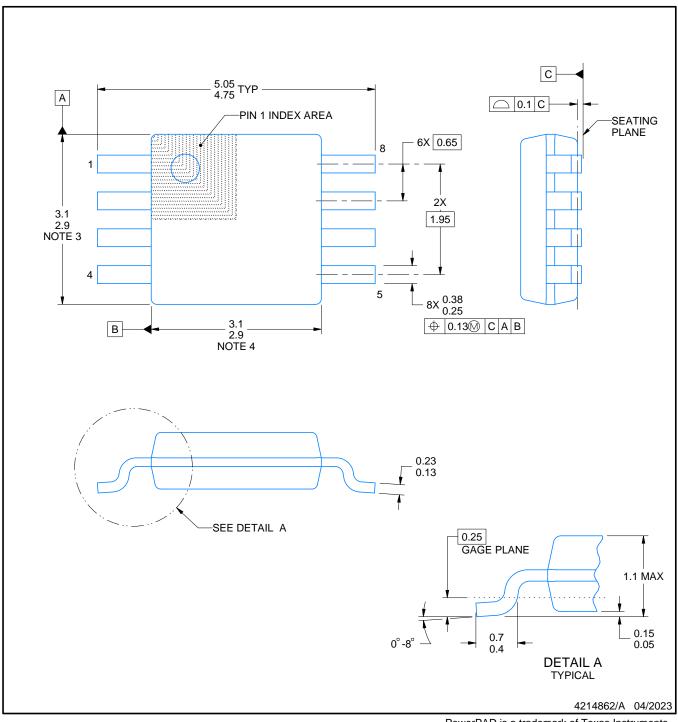
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SMALL OUTLINE PACKAGE



NOTES:

PowerPAD is a trademark of Texas Instruments.

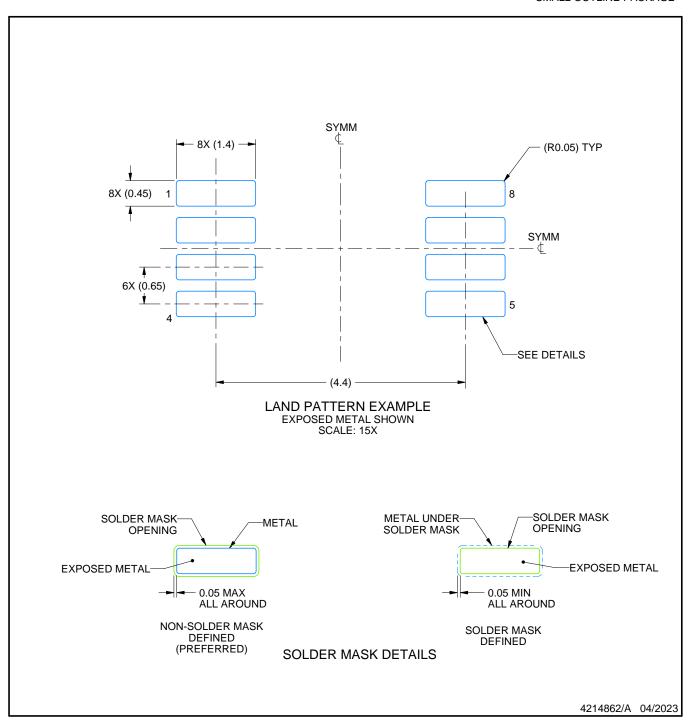
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.



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